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3. (Amended) An electrostatic chucking system comprising:
an electrostatic chuck having an electrode for chucking a semiconductor substrate;
a power supply section for applying a voltage to said electrode;
a voltage control section for controlling the applied voltage; and
a warpage sensor for detecting the amount of warpage arising in the semiconductor substrate held by said electrostatic chuck, wherein a signal output from said warpage sensor is input to said voltage control section to thereby control the applied voltage, wherein
said voltage control section varies and controls the applied voltage stepwise based upon said signal output from said warpage sensor,

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4. (Amended) An electrostatic chucking system comprising:
an electrostatic chuck having an electrode for chucking a semiconductor substrate;
a power supply section for applying a voltage to said electrode;
a voltage control section for controlling the applied voltage; and
a distance sensor for detecting the distance between said electrostatic chuck and the semiconductor substrate held by said electrostatic chuck, wherein a signal output from said distance sensor is input to said voltage control section to thereby control the applied voltage, wherein
said voltage control section varies and controls the applied voltage stepwise based upon said signal output from said distance sensor,

5. (Amended) The electrostatic chucking system according to claim 6, wherein the control of variation in the applied voltage involves either increase or decrease in voltage.

6. (Amended) An electrostatic chucking system comprising:
an electrostatic chuck having an electrode for chucking a semiconductor substrate;
a power supply section for applying a voltage to said electrode; and
a voltage control section for controlling the applied voltage, wherein
said voltage control section varies and controls the applied voltage stepwise, and wherein
the applied voltage is controlled such that a rate at which the temperature change of the
semiconductor substrate falls with a range of 10°C/sec. to 150°C/sec.

7. (Amended) A method of manufacturing a semiconductor device comprising a
step of treating a semiconductor wafer through use of the electrostatic system according to claim
6.

8. (Amended) An apparatus for manufacturing a semiconductor device, said
apparatus comprising the electrostatic system according to claim 6.

REMARKS

At the time of the Office Action dated September 24, 2002, claims 1-8 were pending and rejected in this application. Claims 2-8 have been amended, and care has been exercised to avoid the introduction of new matter. Specifically, claim 3-4 and 6 have been placed in independent form, and consequently, claim 1 has been cancelled. Claims 2, 5 and 7-8 have been amended to address dependency issues arising from the cancellation of claim 1. Applicant submits that the present Amendment does not generate any new matter issue.